December 2004

National Semiconductor

LM3670
Miniature Step-Down DC-DC Converter for Ultra Low Voltage Circuits

General Description

The LM3670 step-down DC-DC converter is optimized for powering ultra-low voltage circuits from a single Li-Ion cell or 3 cell NiMH/NiCd batteries. It provides up to 350 mA load current, over an input voltage range from 2.5V to 5.5V. There are several different fixed voltage output options available as well as an adjustable output voltage version.

The device offers superior features and performance for mobile phones and similar portable applications with complex power management systems. Automatic intelligent switching between PWM low-noise and PFM low-current mode offers improved system control. During full-power operation, a fixed-frequency 1 MHz (typ). PWM mode drives loads from ~70 mA to 350 mA max, with up to 95% efficiency. Hysteretic PFM mode extends the battery life through reduction of the quiescent current to 15 µA (typ) during light current loads and system standby. Internal synchronous rectification provides high efficiency (90 to 95% typ. at loads between 1 mA and 100 mA). In shutdown mode (Enable pin pulled low) the device turns off and reduces battery consumption to 0.1 µA (typ.).

The LM3670 is available in a SOT23-5 package. A high switching frequency - 1 MHz (typ) - allows use of tiny surface-mount components. Only three external surface-mount components, an inductor and two ceramic capacitors, are required.

Features

- V_{OUT} = adj (.7V min), 1.2, 1.5, 1.6, 1.8, 1.875, 2.5, 3.3V
- $2.5V \le V_{IN} \le 5.5V$
- 15 µA typical quiescent current
- 350 mA maximum load capability
- 1 MHz PWM fixed switching frequency (typ.)
- Automatic PFM/PWM mode switching
- Available in fixed output voltages as well as an adjustable version
- SOT23-5 package
- Low drop out operation - 100% duty cycle mode
- Internal synchronous rectification for high efficiency
- Internal soft start
- 0.1 µA typical shutdown current
- Operates from a single Li-Ion cell or 3 cell NiMH/NiCd batteries
- Only three tiny surface-mount external components required (one inductor, two ceramic capacitors)
- Current overload protection

Applications

- Mobile phones
- Hand-Held Radios
- Personal Digital Assistants
- Palm-top PCs
- Portable Instruments
- Battery Powered Devices

Typical Application

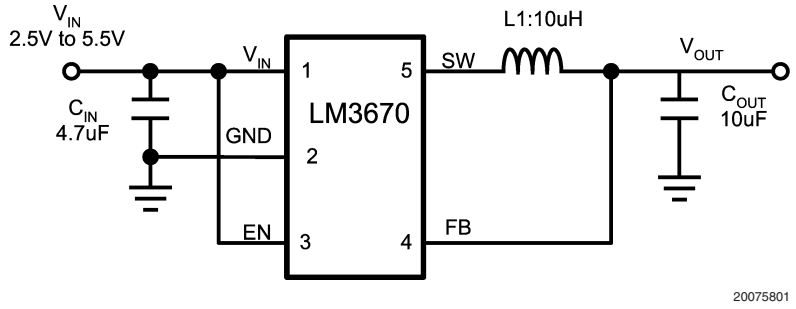


FIGURE 1. 1.8V - Fixed Output Voltage - Typical Application Circuit

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Typical Application (Continued)

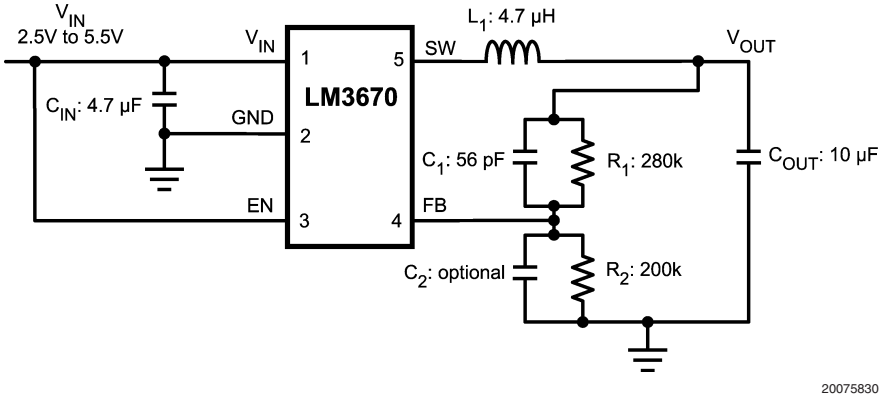
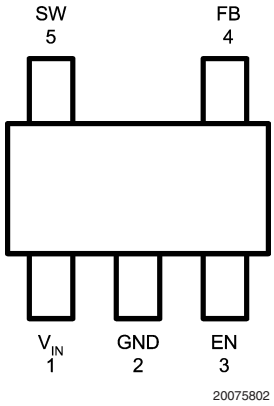


FIGURE 2. 1.2V - Adjustable Output Voltage - Typical Application Circuit

Connection Diagram and Package Mark Information

SOT23-5 Package
NS Package Number XXXX



Note: The actual physical placement of the package marking will vary from part to part.

FIGURE 3. Top View

Pin Descriptions

Pin #	Name	Description
1	V_{IN}	Power supply input. Connect to the input filter capacitor (*Figure 1*).
2	GND	Ground pin.
3	EN	Enable input.
4	FB	Feedback analog input. Connect to the output filter capacitor (*Figure 1*).
5	SW	Switching node connection to the internal PFET switch and NFET synchronous rectifier. Connect to an inductor with a saturation current rating that exceeds the 750 mA max. Switch Peak Current Limit specification.

Ordering Information

Voltage Option (V)	Order Number (Level 95)	SPEC	Package Marking	Supplied As (#/reel)
3.3	LM3670MF-3.3	NOPB	SDEB	1000
	LM3670MFX-3.3	NOPB		3000
	LM3670MF-3.3			1000
	LM3670MFX-3.3			3000
2.5	LM3670MF-2.5	NOPB	SDDB	1000
	LM3670MFX-2.5	NOPB		3000
	LM3670MF-2.5			1000
	LM3670MFX-2.5			3000
1.875	LM3670MF-1.875	NOPB	SEFB	1000
	LM3670MFX-1.875	NOPB		3000
	LM3670MF-1.875			1000
	LM3670MFX-1.875			3000
1.8 *	LM3670MF-1.8	NOPB	SDCB	1000
	LM3670MFX-1.8	NOPB		3000
	LM3670MF-1.8			1000
	LM3670MFX-1.8			3000
1.6	LM3670MF-1.6	NOPB	SDBB	1000
	LM3670MFX-1.6	NOPB		3000
	LM3670MF-1.6			1000
	LM3670MFX-1.6			3000
1.5	LM3670MF-1.5	NOPB	S82B	1000
	LM3670MFX-1.5	NOPB		3000
	LM3670MF-1.5			1000
	LM3670MFX-1.5			3000
1.2	LM3670MF-1.2	NOPB	SCZB	1000
	LM3670MFX-1.2	NOPB		3000
	LM3670MF-1.2			1000
	LM3670MFX-1.2			3000
Adjustable *	LM3670MF-ADJ	NOPB	SDFB	1000
	LM3670MFX-ADJ	NOPB		3000
	LM3670MF-ADJ			1000
	LM3670MFX-ADJ			3000

*Released. Samples available.

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

V_{IN} Pin: Voltage to GND	–0.2V to 6.0V
EN Pin: Voltage to GND	–0.2V to 6.0V
FB, SW Pin:	(GND–0.2V) to (V_{IN} + 0.2V)
Junction Temperature (T_{J-MAX})	–45˚C to +125˚C
Storage Temperature Range	–45˚C to +150˚C
Maximum Lead Temperature (Soldering, 10 sec.)	260˚C

ESD Rating (Note 3)	
Human Body Model:	
VIN,SW,FB,GND	2.0kV
EN	500V
Machine Model:	200V

Operating Ratings (Notes 1, 2)

Input Voltage Range	2.5V to 5.5V
Recommended Load Current	0A to 350 mA
Junction Temperature (T_J) Range	–40˚C to +125˚C
Ambient Temperature (T_A) Range	–40˚C to +85˚C

Thermal Properties

Junction-to-Ambient Thermal Resistance (θ_{JA}) (SOT23-5)	250˚C/W

Electrical Characteristics

Limits in standard typeface are for T_J = 25˚C. Limits in **boldface** type apply over the full operating junction temperature range (–40˚C ≤ T_J ≤ +125˚C). Unless otherwise noted V_{IN} = 3.6V, V_{OUT} = 1.8V, I_O=150mA, EN=V_{IN}

Symbol	Parameter	Condition	Min	Typ	Max	Units
V_{IN}	Input Voltage Range		2.5		5.5	V
V_{OUT}	Fixed Output Voltage	2.5V ≤ V_{IN} ≤ 5.5V I_O = 10 mA	**-1.5**		**+3.0**	%
		2.5V ≤ V_{IN} ≤ 5.5V 0 mA ≤ I_O ≤ 350 mA	**–4.5**		**+3.0**	%
	Adjustable Output Voltage	2.5V ≤ V_{IN} ≤ 5.5V I_O = 10 mA	-1.0		+2.5	%
		2.5V ≤ V_{IN} ≤ 5.5V 0 mA ≤ I_O ≤ 350 mA	-4.0		+2.5	%
	Line Regulation	2.5V ≤ V_{IN} ≤ 5.5V I_O = 10 mA		0.26		%/V
	Load Regulation	150 mA ≤ I_O ≤ 350 mA		0.0014		%/mA
V_{REF}	Internal Reference Voltage			0.5		V
I_{Q_SHDN}	Shutdown Supply Current	T_A=85ºC		0.1	1	µA
I_{Q_PFM}	DC Bias Current into V_{IN}	No load, device is not switching (V_{OUT} forced higher than programmed output voltage)		15	**30**	µA
V_{UVLO}	Minimum V_{IN} below which V_{OUT} will be disabled			**2.4**		V
$R_{DSON\ (P)}$	Pin-Pin Resistance for PFET	V_{IN}=V_{GS}=3.6V		360	**690**	mΩ
$R_{DSON\ (N)}$	Pin-Pin Resistance for NFET	V_{IN}=V_{GS}=3.6V		250	**660**	mΩ
$I_{LKG\ (P)}$	P Channel Leakage Current	V_{DS}=5.5V		0.1	1	µA
$I_{LKG\ (N)}$	N Channel Leakage Current	V_{DS}=5.5V		0.1	1.5	µA
I_{LIM}	Switch Peak Current Limit		**400**	620	**750**	mA
η	Efficiency (V_{IN} = 3.6V, V_{OUT} = 1.8V)	I_{LOAD} = 1 mA		91		%
		I_{LOAD} = 10 mA		94		
		I_{LOAD} = 100 mA		94		
		I_{LOAD} = 200 mA		94		
		I_{LOAD} = 300 mA		92		
		I_{LOAD} = 350 mA		90		

Electrical Characteristics Limits in standard typeface are for T_J = 25˚C. Limits in **boldface** type apply over the full operating junction temperature range (–40˚C ≤ T_J ≤ +125˚C). Unless otherwise noted V_{IN} = 3.6V, V_{OUT} = 1.8V, I_O=150mA, EN=V_{IN} (Continued)

Symbol	Parameter	Condition	Min	Typ	Max	Units
V_{IH}	Logic High Input		**1.3**			V
V_{IL}	Logic Low Input				**0.4**	V
I_{EN}	Enable (EN) Input Current			0.01	**1**	µA
F_{OSC}	Internal Oscillator Frequency	PWM Mode	**550**	1000	**1300**	kHz

Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the component may occur. Operating Ratings are conditions under which operation of the device is guaranteed. Operating Ratings do not imply guaranteed performance limits. For guaranteed performance limits and associated test conditions, see the Electrical Characteristics tables.

Note 2: All voltages are with respect to the potential at the GND pin.

Note 3: The Human body model is a 100 pF capacitor discharged through a 1.5 kΩ resistor into each pin. The machine model is a 200 pF capacitor discharged directly into each pin. MIL-STD-883 3015.7

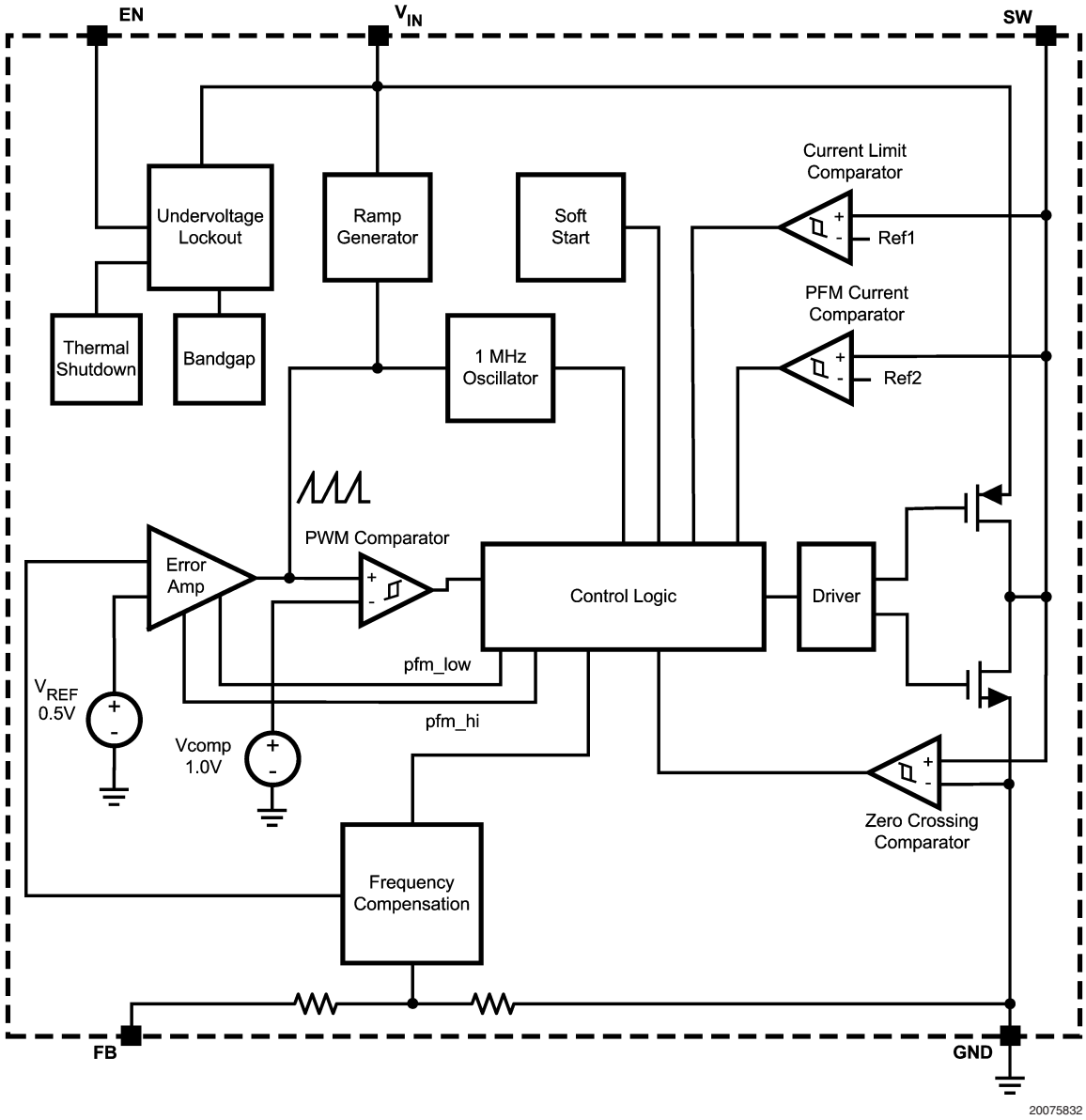
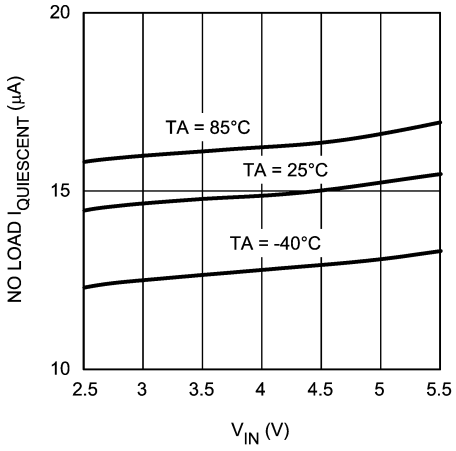


FIGURE 4. Simplified Functional Diagram

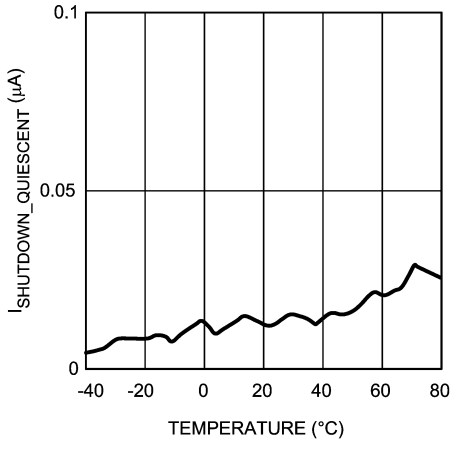
Typical Performance Characteristics (unless otherwise stated: V_{IN}=3.6V, V_{OUT}=1.8V)

I_Q vs. V_{IN} (output pulled above regulation voltage)



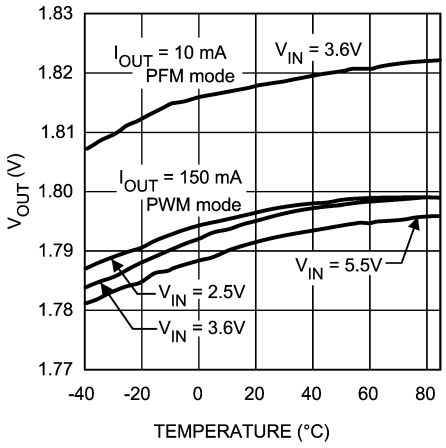
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I_Q Shutdown vs. Temp



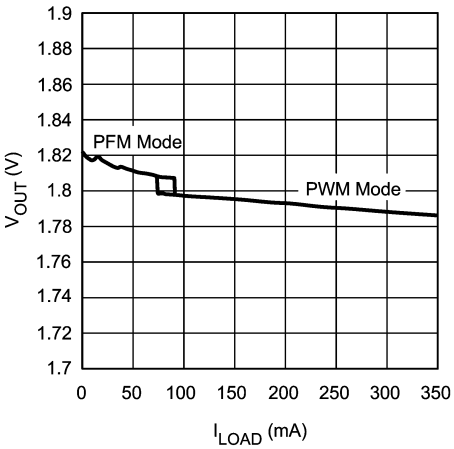
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V_{OUT} vs. V_{IN}



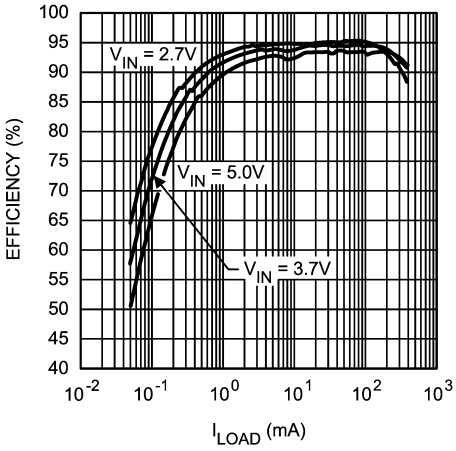
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V_{OUT} vs. I_{OUT}



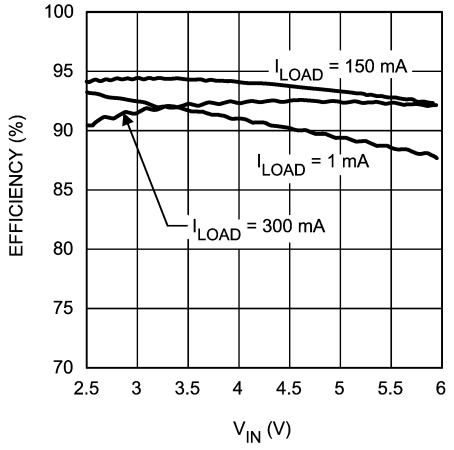
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Efficiency vs. I_{OUT}



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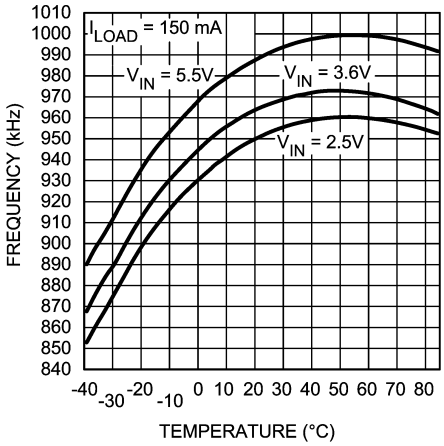
Efficiency vs. V_{IN}



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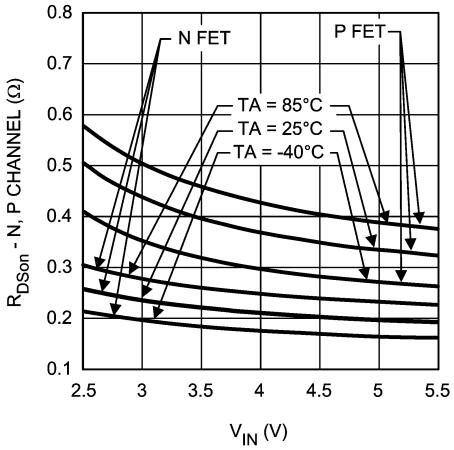
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Frequency vs. Temperature



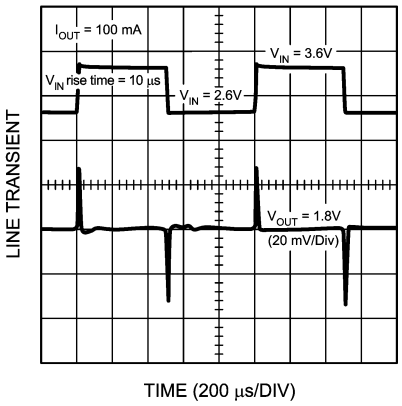
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R_{DSON} vs. V_{IN}
P & N Channel



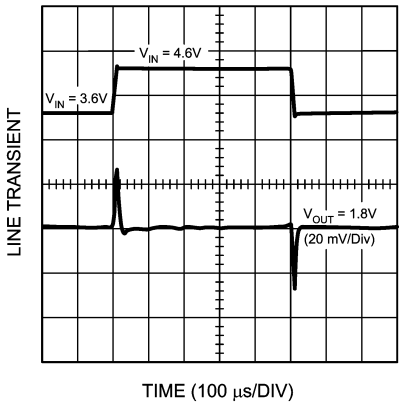
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Line Transient
V_{IN}, V_{OUT} vs. Time
V_{IN} = 2.6V to 3.6V



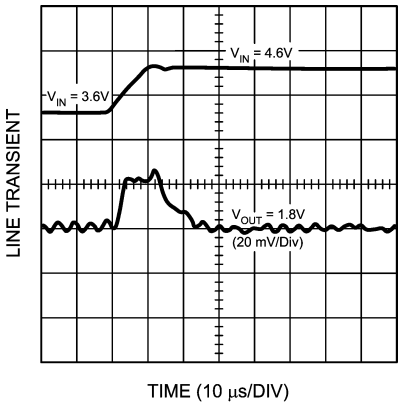
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Line Transient
V_{IN}, V_{OUT} vs. Time
V_{IN} = 3.6V to 4.6V
(I_{LOAD} = 100 mA)



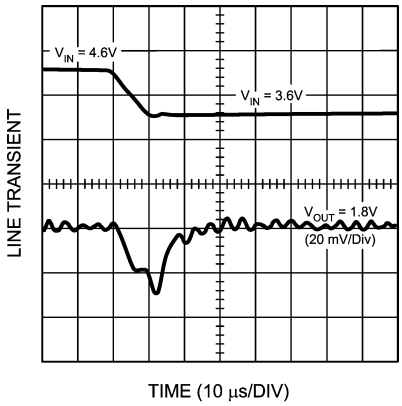
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Line Transient
V_{IN}, V_{OUT} vs. Time
V_{IN} = 3.6V to 4.6V
(I_{LOAD} = 100 mA)



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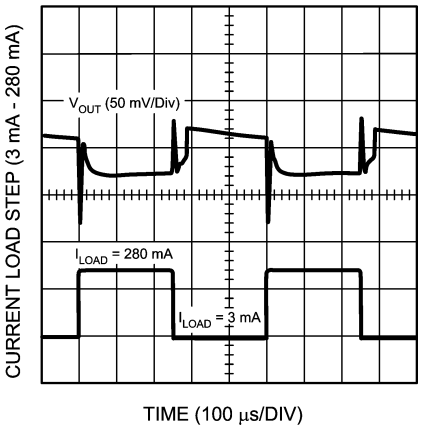
Line Transient
V_{IN}, V_{OUT} vs. Time
V_{IN} = 4.6V to 3.6V
(I_{LOAD} = 100 mA)



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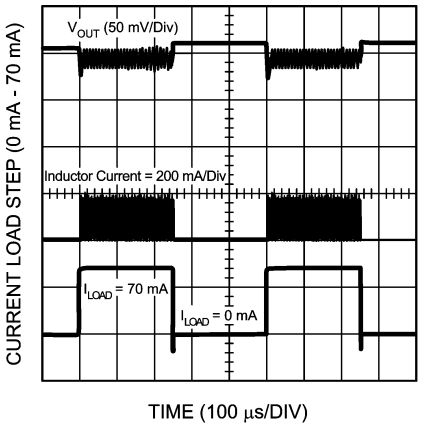
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Load Transient
V_{OUT}, I_{LOAD} vs. Time
I_{LOAD} = 3mA to 280mA



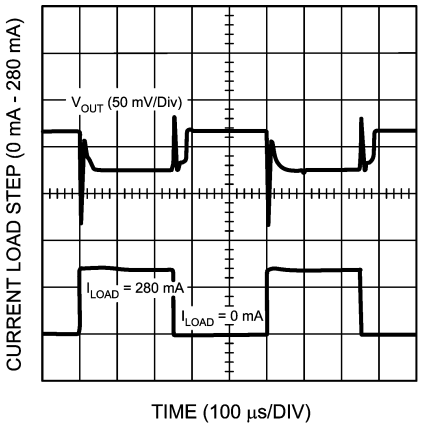
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Load Transient
V_{OUT}, $I_{INDUCTOR}$, I_{LOAD} vs. Time
I_{LOAD} = 0mA to 70mA



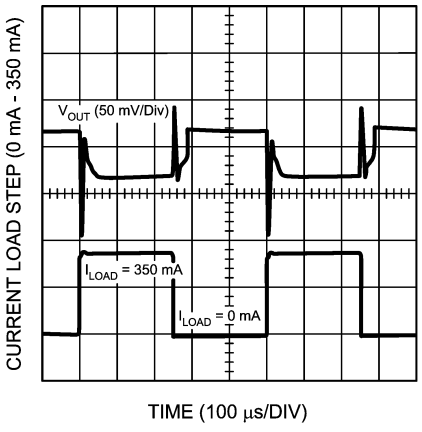
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Load Transient
V_{OUT}, I_{LOAD} vs. Time
I_{LOAD} = 0mA to 280mA



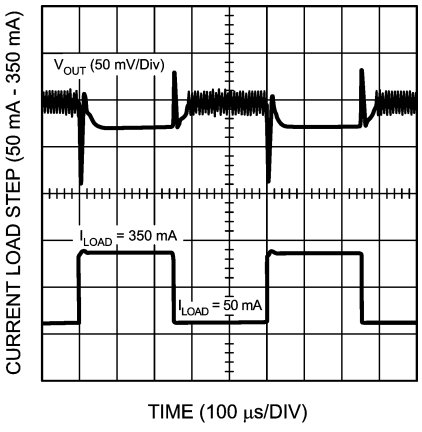
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Load Transient
V_{OUT}, I_{LOAD} vs. Time
I_{LOAD} = 0mA to 350mA



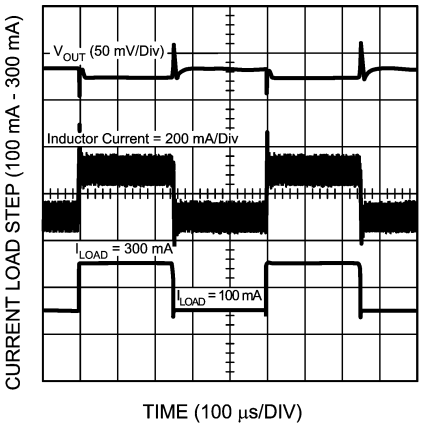
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Load Transient
V_{OUT}, I_{LOAD} vs. Time
I_{LOAD} = 50mA to 350mA



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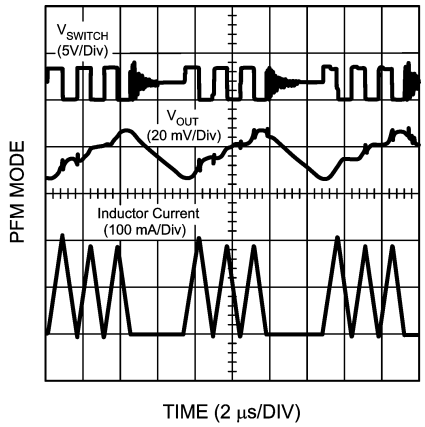
Load Transient
V_{OUT}, I_{LOAD} vs. Time
I_{LOAD} = 100mA to 300mA



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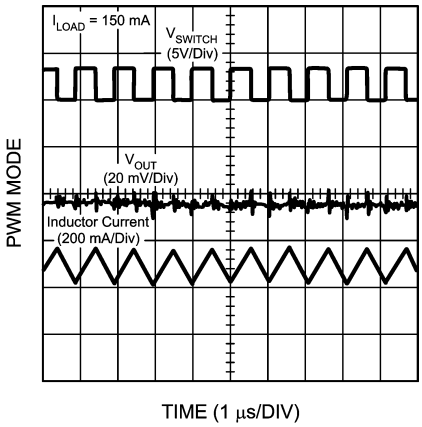
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PFM Mode
V_{SW}, V_{OUT}, $I_{INDUCTOR}$ vs. Time



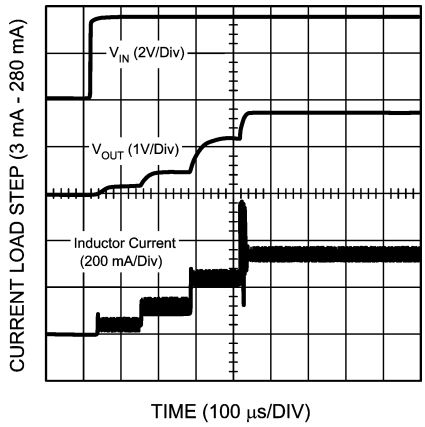
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PWM Mode
V_{SW}, V_{OUT}, $I_{INDUCTOR}$ vs. Time



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Soft Start
V_{IN}, V_{OUT}, $I_{INDUCTOR}$ vs. Time
(I_{LOAD} = 350mA)



20075824

Operation Description

DEVICE INFORMATION

The LM3670, a high efficiency step down DC-DC switching buck converter, delivers a constant voltage from either a single Li-Ion or three cell NiMH/NiCd battery to portable devices such as cell phones and PDAs. Using a voltage mode architecture with synchronous rectification, the LM3670 has the ability to deliver up to 350 mA depending on the input voltage and output voltage (voltage head room), and the inductor chosen (maximum current capability).

There are three modes of operation depending on the current required - PWM, PFM, and shutdown. PWM mode handles current loads of approximately 70 mA or higher. Lighter output current loads cause the device to automatically switch into PFM for reduced current consumption (I_Q = 15 µA typ) and a longer battery life. Shutdown mode turns off the device, offering the lowest current consumption ($I_{Q,\ SHUTDOWN}$ = 0.1 µA typ).

The LM3670 can operate up to a 100% duty cycle (PMOS switch always on) for low drop out control of the output voltage. In this way the output voltage will be controlled down to the lowest possible input voltage.

Additional features include soft-start, under voltage lock out, current overload protection, and thermal overload protection. As shown in *Figure 1*, only three external power components are required for implementation.

CIRCUIT OPERATION

The LM3670 operates as follows. During the first portion of each switching cycle, the control block in the LM3670 turns on the internal PFET switch. This allows current to flow from the input through the inductor to the output filter capacitor and load. The inductor limits the current to a ramp with a slope of

$$\frac{V_{IN}-V_{OUT}}{L}$$

by storing energy in a magnetic field. During the second portion of each cycle, the controller turns the PFET switch

Operation Description (Continued)

off, blocking current flow from the input, and then turns the NFET synchronous rectifier on. The inductor draws current from ground through the NFET to the output filter capacitor and load, which ramps the inductor current down with a slope of

$$\frac{-V_{OUT}}{L}$$

The output filter stores charge when the inductor current is high, and releases it when low, smoothing the voltage across the load.

PWM OPERATION

During PWM operation the converter operates as a voltage-mode controller with input voltage feed forward. This allows the converter to achieve excellent load and line regulation. The DC gain of the power stage is proportional to the input voltage. To eliminate this dependence, feed forward inversely proportional to the input voltage is introduced.

Internal Synchronous Rectification

While in PWM mode, the LM3670 uses an internal NFET as a synchronous rectifier to reduce rectifier forward voltage drop and associated power loss. Synchronous rectification provides a significant improvement in efficiency whenever the output voltage is relatively low compared to the voltage drop across an ordinary rectifier diode.

Current Limiting

A current limit feature allows the LM3670 to protect itself and external components during overload conditions PWM mode implements cycle-by-cycle current limiting using an internal comparator that trips at 620 mA (typ).

PFM OPERATION

At very light loads, the converter enters PFM mode and operates with reduced switching frequency and supply current to maintain high efficiency.

The party will automatically transition into PFM mode when either of two conditions occurs for a duration of 32 or more clock cycles:

A. The inductor current becomes discontinuous

B. The peak PMOS switch current drops below the I_{MODE} level:

$$I_{MODE} < 26\ mA + \frac{V_{IN}}{50\Omega}\ (typ)$$

During PFM operation, the converter positions the output voltage slightly higher than the nominal output voltage during PWM operation, allowing additional headroom for voltage drop during a load transient from light to heavy load. The PFM comparators sense the output voltage via the feedback pin and control the switching of the output FETs such that the output voltage ramps between 0.8% and 1.6% (typ) above the nominal PWM output voltage. If the output voltage is below the 'high' PFM comparator threshold, the PMOS power switch is turned on. It remains on until the output voltage exceeds the 'high' PFM threshold or the peak current exceeds the I_{PFM} level set for PFM mode. The peak current in PFM mode is:

$$I_{PFM} = 117\ mA + \frac{V_{IN}}{64\Omega}\ (typ)$$

Once the PMOS power switch is turned off, the NMOS power switch is turned on until the inductor current ramps to zero. When the NMOS zero-current condition is detected, the NMOS power switch is turned off. If the output voltage is below the 'high' PFM comparator threshold (see *Figure 5*), the PMOS switch is again turned on and the cycle is repeated until the output reaches the desired level. Once the output reaches the 'high' PFM threshold, the NMOS switch is turned on briefly to ramp the inductor current to zero and then both output switches are turned off and the part enters an extremely low power mode. Quiescent supply current during this 'sleep' mode is less than 30 µA, which allows the part to achieve high efficiencies under extremely light load conditions. When the output drops below the 'low' PFM threshold, the cycle repeats to restore the output voltage to ~1.6% above the nominal PWM output voltage.

If the load current should increase during PFM mode (see *Figure 5*) causing the output voltage to fall below the 'low2' PFM threshold, the part will automatically transition into fixed-frequency PWM mode.

Operation Description (Continued)

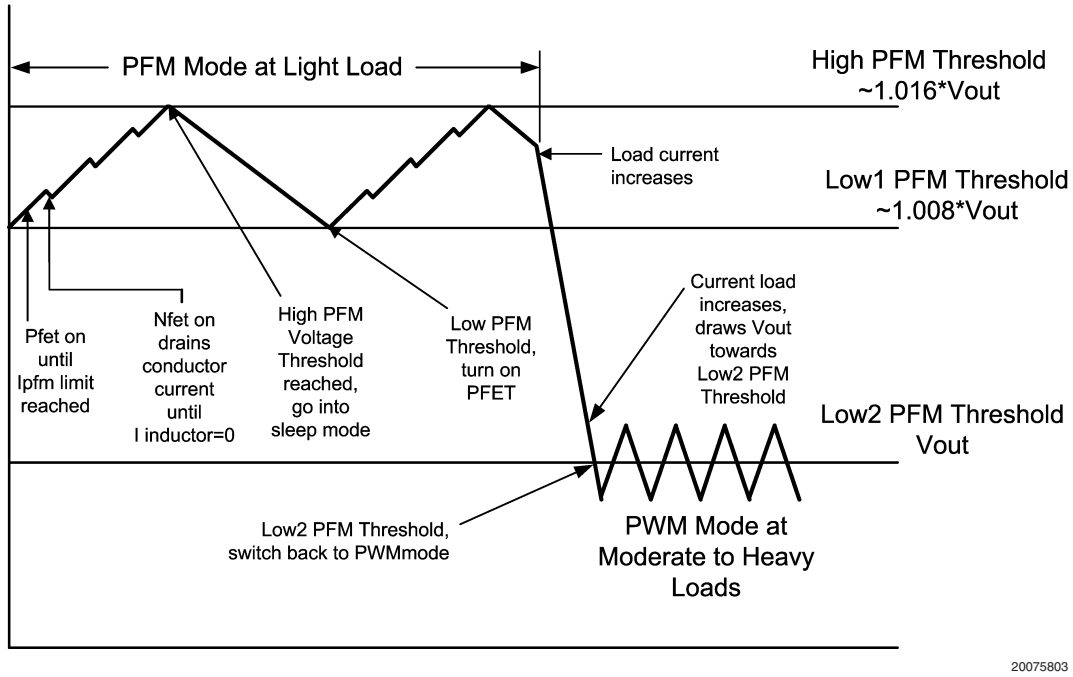


FIGURE 5. Operation in PFM Mode and Transfer to PWM Mode

Soft-Start

The LM3670 will have a soft-start circuit that limits in-rush current during start-up. Typical currents and times are:

Current (mA)	Duration (µSec)
0	32
70	224
140	256
280	256
620	until soft start ends

Note 4: The first 32µS are to allow the bias currents to stabilize

LDO - Low Drop Out Operation

The LM3670 can operate at 100% duty cycle (no switching, PMOS switch completely on) for low drop out support of the output voltage. In this way the output voltage will be controlled down to the lowest possible input voltage.

The minimum input voltage needed to support the output voltage is

$$V_{IN,MIN} = I_{LOAD} * (R_{DSON,PFET} + R_{INDUCTOR}) + V_{OUT}$$

- I_{LOAD} Load current
- $R_{DSON,PFET}$ Drain to source resistance of PFET switch in the triode region
- $R_{INDUCTOR}$ Inductor resistance

Application Information

OUTPUT VOLTAGE SELECTION FOR ADJUSTABLE LM3670

The output voltage of the adjustable parts can be programmed through the resistor network connected from V_{OUT} to V_{FB} the to GND. V_{OUT} will be adjusted to make V_{FB} equal to .5V. The resistor from V_{FB} to GND (R2) should be at least 100KΩ to keep the current sunk through this network well below the 15µA quiescent current level (PFM mode with no switching) but large enough that it is not susceptible to noise. If R_2 is 200KΩ, and given the V_{FB} is .5V, then the current through the resistor feedback network will be 2.5µA (I_{FB} =.5V/R_2). The output voltage formula is:

$$V_{OUT} = V_{FB} * (\frac{R_1}{R_2} + 1)$$

- V_{OUT} Output Voltage (V)
- V_{FB} Feedback Voltage (.5V typ)
- R_1 Resistor from V_{OUT} to V_{FB} (Ω)
- R_2 Resistor from V_{OUT} to GND (Ω)

For any output voltage greater than or equal to .8V a frequency zero must be added at 10KHz for stability. The formula is:

$$C_1 = \frac{1}{2 * \pi * R_1 * 10\ kHz}$$

For output voltages between .7 and .8V a pole must also be placed at 10KHz as well. The lowest output voltage possible is .7V. At the low voltages the duty cycle is very small. In addition, as the input voltage increases the duty cycle decreases even further. Since the duty cycle is so low any change due to noise is an appreciable percentage. In other words, it is susceptible to noise. The C_1 and C_2 act as noise filters at this point rather than frequency poles and zeroes. If tghe pole and zero are at the sasme frequency the formula is:

$$C_2 = \frac{1}{2 * \pi * R_2 * 10\ kHz}$$

A pole can be usesd at higher output voltages too. For example, in the table "Adjustable LM3670 Configurations for Various VOUT" *Table 3* there is an entry for 1.24V with both a pole and zero at approximately 10KHz for noise rejection.

INDUCTOR SELECTION

There are two main considerations when choosing an inductor; the inductor current should not saturate, and the inductor current ripple is small enough to achieve the desired output voltage ripple.

There are two methods to choose the inductor current rating.

Method 1:

The total current is the sum of the load and the inductor ripple current. This can be written as

$$I_{MAX} = I_{LOAD} + \frac{I_{RIPPLE}}{2}$$

$$V_{OUT} = I_{LOAD} + (\frac{V_{IN}-V_{OUT}}{2 * L})(\frac{V_{OUT}}{V_{IN}})(\frac{1}{f})$$

- I_{LOAD} load current
- V_{IN} input voltage
- L inductor
- f switching frequency
- I_{RIPPLE} peak-to-peak

Method 2:

A more conservative approach is to choose an inductor that can handle the current limit of 700 mA.

Given a peak-to-peak current ripple (I_{PP}) the inductor needs to be at least

$$L >= (\frac{V_{IN} - V_{OUT}}{I_{PP}}) * (\frac{V_{OUT}}{V_{IN}}) * (\frac{1}{f})$$

A 10 µH inductor with a saturation current rating of at least 800 mA is recommended for most applications. The inductor's resistance should be less than around 0.3Ω for good efficiency. *Table 1* lists suggested inductors and suppliers. For low-cost applications, an unshielded bobbin inductor is suggested. For noise critical applications, a toroidal or shielded-bobbin inductor should be used. A good practice is to lay out the board with overlapping footprints of both types for design flexibility. This allows substitution of a low-noise toroidal inductor, in the event that noise from low-cost bobbin models is unacceptable.

INPUT CAPACITOR SELECTION

A ceramic input capacitor of 4.7 µF is sufficient for most applications. A larger value may be used for improved input voltage filtering. The input filter capacitor supplies current to the PFET switch of the LM3670 in the first half of each cycle and reduces voltage ripple imposed on the input power source. A ceramic capcitor's low ESR provides the best noise filtering of the input voltage spikes due to this rapidly changing current. Select an input filter capacitor with a surge current rating sufficient for the power-up surge from the input power source. The power-up surge current is approximately the capacitor's value (µF) times the voltage rise rate (V/µs). The input current ripple can be calculated as:

$$I_{RMS} = I_{OUTMAX} * \sqrt{\frac{V_{OUT}}{V_{IN}} * (1 - \frac{V_{OUT}}{V_{IN}})}$$

The worst case IRMS is:

$$IRMS = \frac{IRMS}{2} \qquad \text{(duty cycle = 50\%)}$$

Application Information (Continued)

TABLE 1. Suggested Inductors and Their Suppliers

Model	Vendor	Phone	FAX
IDC2512NB100M	Vishay	408-727-2500	408-330-4098
DO1608C-103	Coilcraft	847-639-6400	847-639-1469
ELL6RH100M	Panasonic	714-373-7366	714-373-7323
CDRH5D18-100	Sumida	847-956-0666	847-956-0702

OUTPUT CAPACITOR SELECTION

The output filter capacitor smoothes out current flow from the inductor to the load, helps maintain a steady output voltage during transient load changes and reduces output voltage ripple. These capacitors must be selected with sufficient capacitance and sufficiently low ESR to perform these functions.

The output ripple current can be calculated as:

Voltage peak-to-peak ripple due to capacitance =

$$V_{PP\text{-}C} = \frac{I_{PP}}{f*8*C}$$

Voltage peak-to-peak ripple due to ESR =

$$V_{OUT} = V_{PP\text{-}ESR} = I_{PP} * R_{ESR}$$

Voltage peak-to-peak ripple, root mean squared =

$$V_{PP\text{-}RMS} = \sqrt{V_{PP\text{-}C}^{\,2} + V_{PP\text{-}ESR}^{\,2}}$$

Note that the output ripple is dependent on the current ripple and the equivalent series resistance of the output capacitor (R_{ESR}).

Because these two components are out of phase the rms value is used. The R_{ESR} is frequency dependent (as well as temperature dependent); make sure the frequency of the R_{ESR} given is the same order of magnitude as the switching frequency.

TABLE 2. Suggested Capacitors and Their Suppliers

Model	Type	Vendor	Phone	FAX
10 µF for C_{OUT}				
VJ1812V106MXJAT	Ceramic	Vishay	408-727-2500	408-330-4098
LMK432BJ106MM	Ceramic	Taiyo-Yuden	847-925-0888	847-925-0899
JMK325BJ106MM	Ceramic	Taiyo-Yuden	847-925-0888	847-925-0899
4.7 µF for C_{IN}				
VJ1812V475MXJAT	Ceramic	Vishay	408-727-2500	408-330-4098
EMK325BJ475MN	Ceramic	Taiyo-Yuden	847-925-0888	847-925-0899
C3216X5R0J475M	Ceramic	TDK	847-803-6100	847-803-6296

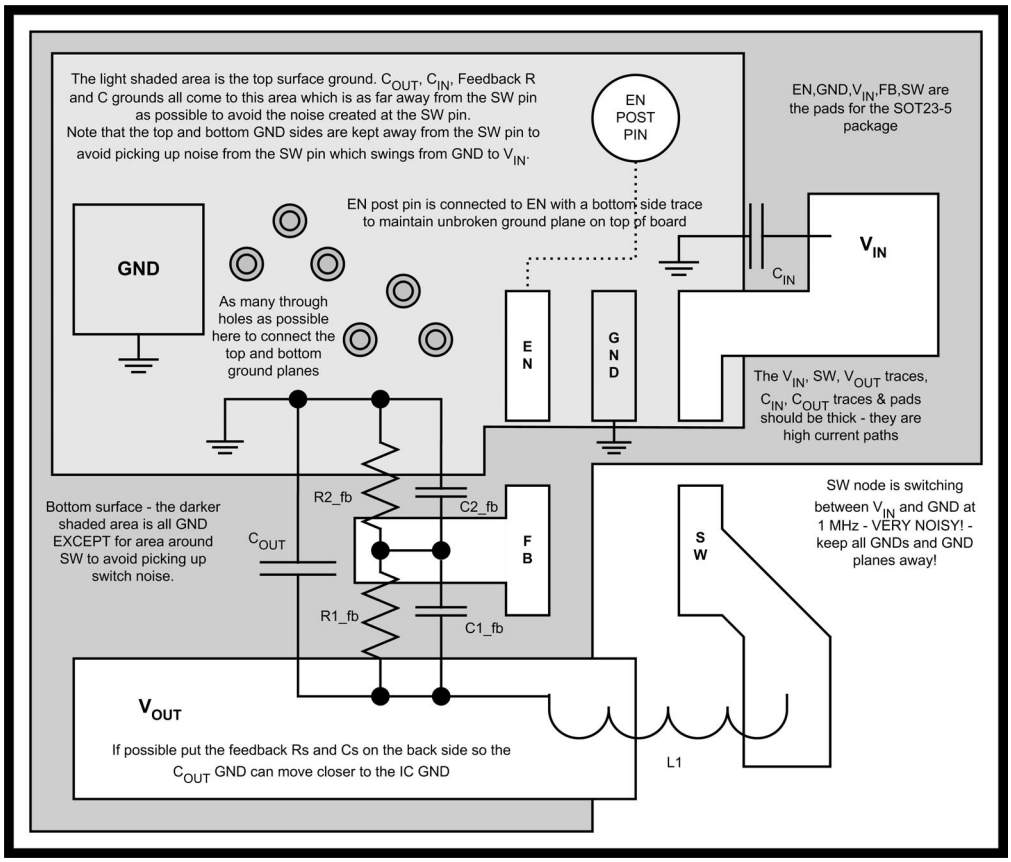
TABLE 3. Adjustable LM3670 Configurations for Various V_{OUT}

VOUT (V)	R1 (KΩ)	R2 (KΩ)	C1 (pF)	C2 (pF)	L (µH)	CIN (µF)	COUT (µF)
0.7	80.6	200	200	150	4.7	4.7	10
0.8	120	200	130	none	4.7	4.7	10
0.9	160	200	100	none	4.7	4.7	10
1.0	200	200	82	none	4.7	4.7	10
1.1	240	200	68	none	4.7	4.7	10
1.2	280	200	56	none	4.7	4.7	10
1.24	300	200	56	none	4.7	4.7	10
1.24	221	150	75	120	4.7	4.7	10
1.5	402	200	39	none	10	4.7	10
1.6	442	200	39	none	10	4.7	10
1.7	487	200	33	none	10	4.7	10
1.875	549	200	30	none	10	4.7	14.7 **Note:** (10 ‖ 4.7)
2.5	806	200	22	82	10	4.7	22

Application Information (Continued)

BOARD LAYOUT CONSIDERATIONS

PC board layout is an important part of DC-DC converter design. Poor board layout can disrupt the performance of a DC-DC converter and surrounding circuitry by contributing to EMI, ground bounce, and resistive voltage loss in the traces. These can send erroneous signals to the DC-DC converter IC, resulting in poor regulation or instability.



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FIGURE 6. Board Layout Design Rules for the LM3670

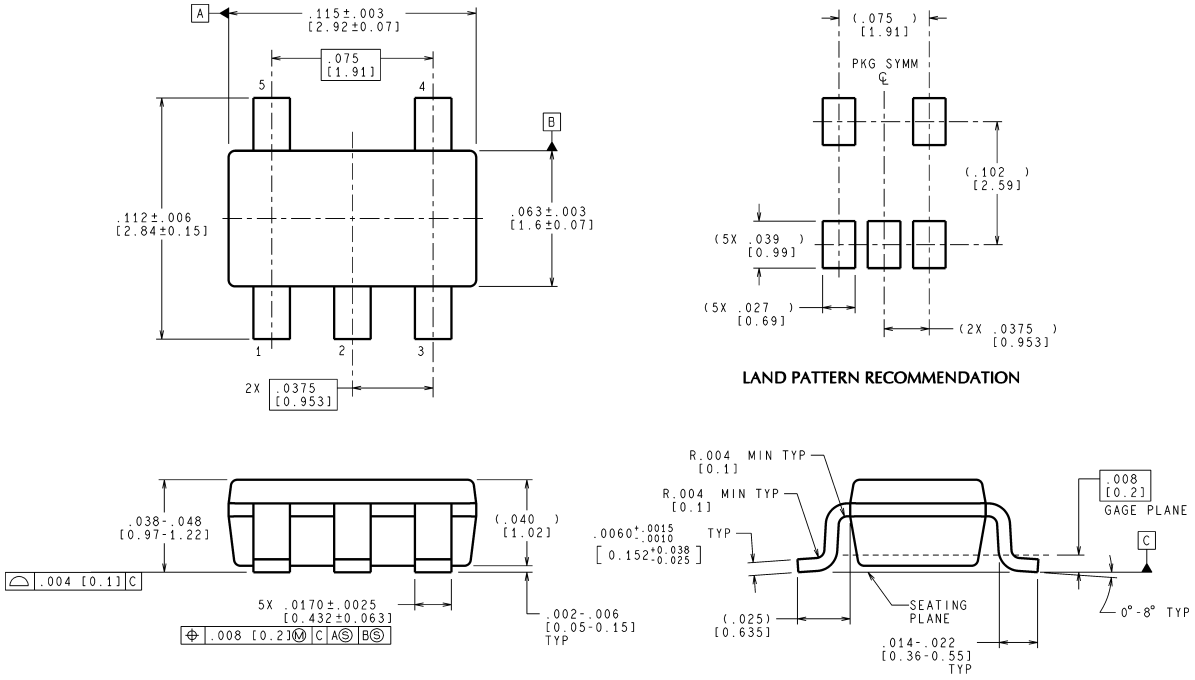
Good layout for the LM3670 can be implemented by following a few simple design rules, as illustrated in .

1. Place the LM3670 on TBDmil (TBD/1000 in.) pads. *Place the LM3670, inductor and filter capacitors close together and make the traces short.* The traces between these components carry relatively high switching currents and act as antennas. Following this rule reduces radiated noise. Place the capacitors and inductor within 0.2 in. (5 mm) of the LM3670.
2. *Arrange the components so that the switching current loops curl in the same direction.* During the first half of each cycle, current flows from the input filter capacitor, through the LM3670 and inductor to the output filter capacitor and back through ground, forming a current loop. In the second half of each cycle, current is pulled up from ground, through the LM3670 by the inductor, to the output filter capacitor and then back through ground, forming a second current loop. Routing these loops so the current curls in the same direction prevents magnetic field reversal between the two half-cycles and reduces radiated noise.
3. *Connect the ground pins of the LM3670, and filter capacitors together using generous component-side copper fill as a pseudo-ground plane. Then, connect this to the ground-plane (if one is used) with several vias.* This reduces ground-plane noise by preventing the switching currents from circulating through the ground plane. It also reduces ground bounce at the LM3670 by giving it a low-impedance ground connection.
4. *Use wide traces between the power components and for power connections to the DC-DC converter circuit.* This reduces voltage errors caused by resistive losses across the traces.
5. *Route noise sensitive traces, such as the voltage feedback path, away from noisy traces between the power components.* The voltage feedback trace must remain close to the LM3670 circuit and should be direct but should be routed opposite to noisy components. This reduces EMI radiated onto the DC-DC converter's own voltage feedback trace.
6. *Place noise sensitive circuitry, such as radio IF blocks, away from the DC-DC converter, CMOS digital blocks and other noisy circuitry.* Interference with noise-sensitive circuitry in the system can be reduced through distance.

Application Information (Continued)

In mobile phones, for example, a common practice is to place the DC-DC converter on one corner of the board, arrange the CMOS digital circuitry around it (since this also generates noise), and then place sensitive preamplifiers and IF stages on the diagonally opposing corner. Often, the sensitive circuitry is shielded with a metal pan and power to it is post-regulated to reduce conducted noise, using low-dropout linear regulators.

Physical Dimensions inches (millimeters) unless otherwise noted



CONTROLLING DIMENSION IS INCH
VALUES IN [ ] ARE MILLIMETERS

MF05A (Rev B)

5-Lead SOT23-5 Package
NS Package Number MF05A

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